

In the Claims:

1. (currently amended) An oxide sintered body ~~essentially consisting of~~ comprising: indium oxide and containing titanium, wherein the titanium is contained such that the atomic ratio of Ti/In is in the a range from 0.003 to 0.1200.019, and wherein the specific resistance is ~~1 k cm or less~~ 1 k Ohm cm or less.

2. (currently amended) the oxide sintered body of claim 1, wherein the specific resistance is 1×10^{-2} Ohm cm or less.

3. cancelled.

4. (currently amended) The oxide sintered body of Claim 3, wherein further comprising tin is ~~contained~~ as an impurity in an amount such that the atomic ratio of Sn/In is 0.0025 or less.

5. (currently amended) The oxide sintered body of Claim 1, ~~wherein the~~ further comprising a main phase ~~is only the~~ of one of a crystal phase of indium oxide having a bixbyite type structure with titanium contained in solid solution, ~~or the main phase is a~~ and of a mixture of the a crystal phase of indium oxide having a bixbyite type structure with titanium contained in solid solution and the a crystal phase of an indium titanate compound.

6. (currently amended) ~~The~~ A method for providing an oxide sintered body, ~~of Claim 1, the~~ oxide sintered body comprising indium oxide and titanium, wherein the titanium is contained such that an atomic ratio of Ti/In is in a range of 0.003 to 0.019 and wherein a specific resistance is 1 k Ohm cm or less, the method comprising the steps of: ~~produced~~

producing such that raw materials of indium oxide powder and titanium oxide powder having an average particle size of ~~1-10~~ 1 μm or less; ~~are mixed~~

mixing the raw materials in a wet mill; ~~formed~~

forming the mixed raw materials with a cold isostatic press, and ~~sintered~~

sintering the formed and mixed raw materials under oxygen-control.

7. (currently amended) The oxide sintered body of Claim 1, wherein ~~an~~ crystal phase of titanium oxide is not detected by powder X-ray diffraction measurement.

10/694,704

8. (original) The oxide sintered body of Claim 1, wherein the relative density is 95% or greater.

9. (currently amended) The oxide sintered body of Claim 1, wherein ~~the~~ a surface roughness R_{max} of the surface on ~~the~~ a side where sputtering is performed is $3.0 \mu\text{m}$ or less.

10. (currently amended) A sputtering target, ~~wherein the oxide sintered body of Claim 1~~ comprising:

an oxide sintered body comprising indium oxide and titanium, wherein the titanium is contained such that an atomic ratio of Ti/In is in a range of 0.003 to 0.019; and

wherein a specific resistance is 1 k Ohm cm or less and is applied to a metal plate for cooling.

11. (currently amended) A sputtering target according to Claim 10 for use in manufacturing a transparent conductive film having a specific resistance $1 \times 10^{-3} \text{ Ohm cm}$ or less.

12. (currently amended) A sputtering target according to Claim 10 for use in manufacturing a low resistant, transparent conductive film having a specific resistance $5.5 \times 10^{-4} \text{ Ohm cm}$ or less.

13. (previously presented) A sputtering target according to Claim 10 for use in manufacturing a transparent conductive film having an average transmittance of infrared rays in the wavelength range from 1000 nm to 1400 nm is at least 60 % for the film itself.

14. (currently amended) A method of manufacturing an oxide transparent electrode film, the method comprising the steps of: wherein

using the a sputtering target of Claim 10 is used the sputtering target comprising an oxide sintered body comprising indium oxide and titanium, wherein the titanium is contained such that an atomic ratio of Ti/In is in a range of 0.003 to 0.019; and

wherein a specific resistance is $1 \times 10^{-2} \text{ k Ohm cm}$ or less and using a DC sputtering method is used for film forming. for forming the film.

15. (new) The oxide sintered body of Claim 3, further comprising a main phase of one of a crystal phase of indium oxide having a bixbyite type structure with titanium contained in solid solution, and of a mixture of a crystal phase of indium oxide having a bixbyite type structure with titanium contained in solid solution and a crystal phase of an indium titanate compound.

16. (new) The oxide sintered body of Claim 4, further comprising a main phase of one of a crystal phase of indium oxide having a bixbyite type structure with titanium contained in solid solution, and of a mixture of a crystal phase of indium oxide having a bixbyite type structure with titanium contained in solid solution and a crystal phase of an indium titanate compound.

17. (new) The oxide sintered body of Claim 3, wherein a crystal phase of titanium oxide is not detected by powder X-ray diffraction measurement.

18. (new) The oxide sintered body of Claim 4, wherein a crystal phase of titanium oxide is not detected by powder X-ray diffraction measurement.

19. (New) A sputtering target according to Claim 11 for use in manufacturing a transparent conductive film having an average transmittance of infrared rays in the wavelength range from 1000 nm to 1400 nm is at least 60 % for the film itself.

20. (new) A sputtering target according to Claim 12 for use in manufacturing a transparent conductive film having an average transmittance of infrared rays in the wavelength range from 1000 nm to 1400 nm is at least 60 % for the film itself.